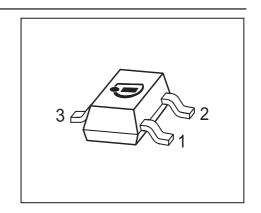


Silicon N-Channel MOSFET Triode

- For high-frequency stages up to 300 MHz preferably in FM applications
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101







ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration					Package	
BF999	LBs	1=G	2=D	3=S	-	1	-	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	20	V
Continuous drain current	I _D	30	mA
Gate-source peak current	± I _{GSM}	10	mA
Total power dissipation	P _{tot}	200	mW
T _S ≤ 76 °C			
Storage temperature	$T_{ m stg}$	-55 150	°C
Channel temperature	T_{ch}	150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Channel - soldering point ²⁾	R _{thchs}	≤ 370	K/W

1

¹Pb-containing package may be available upon special request

 $^{^{2}}$ For calculation of R_{thJA} please refer to Application Note Thermal Resistance



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values		Unit	
		min.	typ.	max.	
DC Characteristics		•	•	•	
Drain-source breakdown voltage	V _{(BR)DS}	20	-	-	V
$I_{\rm D} = 10 \ \mu \rm A, -V_{\rm GS} = 4 \ \rm V$, ,				
Gate-source breakdown voltage	±V _{(BR)GSS}	6.5	-	12	
$\pm I_{GS} = 10 \text{ mA}, \ V_{DS} = 0$, ,				
Gate-source leakage current	± I _{GSS}	-	-	50	nA
$\pm V_{GS} = 5 \text{ V}, \ V_{DS} = 0$					
Drain current	I _{DSS}	5	10	16	mA
$V_{DS} = 10 \text{ V}, \ V_{GS} = 0$					
Gate-source pinch-off voltage	-V _{GS(p)}	-	0.8	1.5	V
$V_{\rm DS} = 10 \text{ V}, I_{\rm D} = 20 \mu\text{A}$, ,				

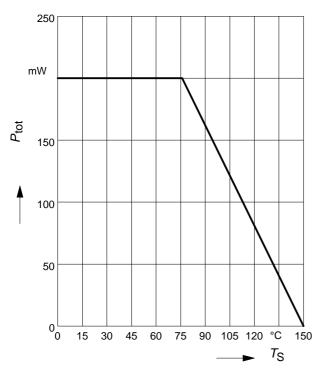
Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics	,	,		•	
Forward transconductance	g_{fs}	14	20	-	mS
$V_{\rm DS} = 10 \text{ V}, I_{\rm D} = 10 \text{ mA}$					
Gate input capacitance	$C_{ m gss}$	-	2.5	-	pF
$V_{DS} = 10 \text{ V}, I_{D} = 10 \text{ mA}, f = 10 \text{ MHz}$					
Output capacitance	$C_{\sf dss}$	-	0.9	-	pF
$V_{DS} = 10 \text{ V}, I_{D} = 10 \text{ mA}, f = 10 \text{ MHz}$					
Power gain	G_{p}	-	27	-	dB
$V_{\rm DS}$ = 10 V, $I_{\rm D}$ = 10 mA, f = 45 MHz					
Noise figure	F	-	2.1	-	dB
$V_{DS} = 10 \text{ V}, I_{D} = 10 \text{ mA}, f = 45 \text{ MHz}$					



Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$

Output characteristics $I_D = f(V_{DS})$



18
mA

0.3V

14

0.2V

0.1V

0.1V

0.1V

-0.1V

-0.4V

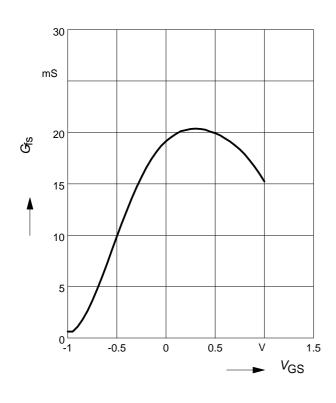
2

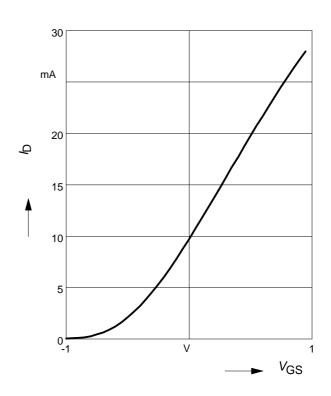
0

VDS

Gate transconductance $g_{fS} = f(V_{GS})$

Drain current $I_D = (V_{GS})$

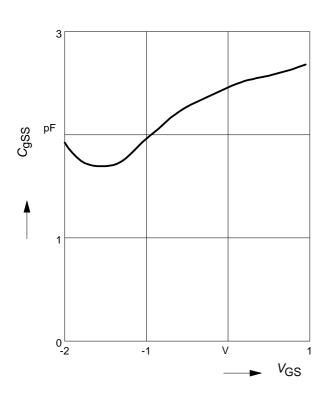


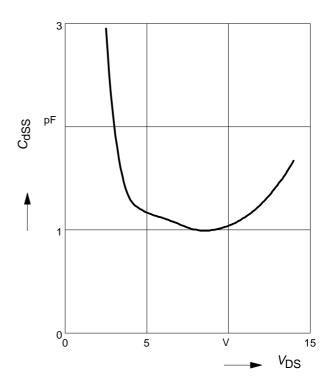




Gate input capacitance $C_{gss} = f(V_{GS})$

Output capacitance $C_{dss} = f(V_{DS})$

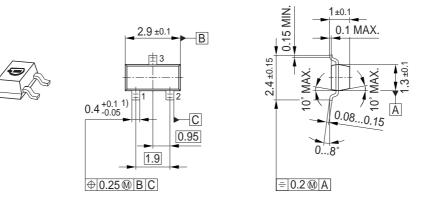




4

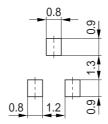


Package Outline

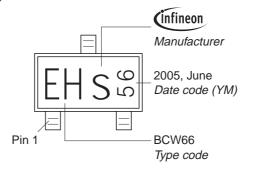


1) Lead width can be 0.6 max. in dambar area

Foot Print

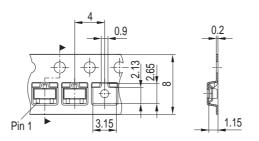


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



5



Edition 2006-02-01 Published by Infineon Technologies AG 81726 München, Germany © Infineon Technologies AG 2007. All Rights Reserved.

Attention please!

The information given in this dokument shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

6

2007-04-20

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Infineon:

BF999E6327HTSA1